

501.36931X00  
Expedited Procedure Requested  
Amendment Under 37 CFR 1.116  
Group 2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): IWASAKI, et al.  
Serial No.: 09/255,856  
Filed: February 23, 1999  
For: SEMICONDUCTOR DEVICE WITH LAYERED INTERCONNECT  
STRUCTURE  
Group: 2813  
Examiner: S. Smoot

AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner for Patents  
Box AF  
Washington, D.C. 20231

May 14, 2001

Sir:

In response to the Office Action mailed December 11,  
2000, please amend the above-identified application as  
follows:

IN THE CLAIMS

Please cancel claims 8, 21 and 26 without prejudice or  
disclaimer, and amend the claims remaining in the application  
as follows:

1. (Amended) A semiconductor device with a multilayered  
structure comprising a copper film interconnect formed on one  
primary surface of a semiconductor substrate, and a  
neighboring film formed in contact with said copper film  
interconnect, wherein said neighboring film is formed of a